

IN THE SPECIFICATION:

Please amend/replace the Title of the Invention for the instant application as follows:

**MAGNETIC TUNNEL JUNCTION DEVICE AND MEMORY DEVICE
INCLUDING METHOD OF MANUFACTURING THE SAME**

Please amend/replace paragraphs [0006] and [0023] of the instant application as follows:

[0006] FIG. 9 shows an example of the basic structure of the MRAM. FIG. 9(A) shows a perspective view of the MRAM, and FIG. 9(B) schematically shows a circuit block diagram. FIG. 9(C) is a cross-section of an example of the structure of the MRAM. Referring to FIG. 9(A), in an MRAM, a word line WL and a bit line BL are disposed in an intersecting manner, with an MRAM cell disposed at each intersection. As shown in FIG. 9(B), the MRAM cell disposed at the intersection of a word line and a bit line comprises a MTJ device and a MOSFET directly connected to the MTJ device. Stored information can be read by reading the resistance value of the MTJ device that functions as a load resistance, using the MOSFET. The stored information can be rewritten by applying a magnetic field to the MTJ device, for example. As shown in FIG. 9(C), an MRAM memory cell comprises a MOSFET 100 including a source region [[105]]103 and a drain region [[103]]105 both formed inside a p-type Si substrate 101, and a gate electrode 111 formed on a channel region that is defined between the source and drain regions. The MRAM also comprises a MTJ device 117. The source region [[105]]103 is grounded via a source junction 113, and the drain region 105 is connected to a bit line BL via a drain junction 115 and the MTJ device. A word line WL is connected to the gate electrode 111 in a region that is not shown.

[0023] ~~Fig. 8~~Figs. 8(A) and 8(B) show~~[[s]]~~ the structure of the MTJ device and its operating principle.